

MOS field-effect transistors

Type N channel	Maximum ratings				Characteristics ($T_{amb} = 25^\circ\text{C}$)					Package outlines	
	V_{DS} V	I_D mA	T_j $^\circ\text{C}$	P_{tot} mW	g_{fs} mS	G dB	V_{DS} V	I_D mA	f MHz	Pin configuration No.	Type
BF 989	20	30	150	200	12	16,5	15	7	800	13	SOT 143
BF 993	20	30	150	200	25	26	15	10	200	13	SOT 143
BF 994	20	30	150	200	17	25	15	10	200	13	SOT 143
BF 995	20	30	150	200	15	23	15	10	200	13	SOT 143
BF 996	20	30	150	200	17	18	15	10	800	13	SOT 143

RF transistors

Type PNP = P NPN = N	Maximum ratings				Characteristics ($T_{amb} = 25^\circ\text{C}$)					Package outlines	
	V_{CEO} V	I_C mA	P_{tot} mW	h_{FE} -	I_{CE} mA	V_{CE} V	I_{CBO} nA	f_T MHz	Pin configuration No.	Type	
BF 554 N	20	30	150	> 50	1	10	-	260	14	SOT 23	
BF 599 N	25	25	150	> 38	7	10	< 100	550	14	SOT 23	
BF 799 N	20	50	220	> 40	20	10	< 100	700	14	SOT 23	
BF 550 P	-40	-25	110	> 50	-1	-10	< -50	375	15	SOT 23	
BF 568 P	-35	-30	220	> 25	-1	-10	< -100	1100	15	SOT 23	
BF 569 P	-35	-30	220	> 25	-3	-10	< -100	850	15	SOT 23	
BF 579 P	-20	-30	110	> 20	-10	-10	< -100	1600	15	SOT 23	
BF 660 P	-30	-25	150	> 30	-3	-10	< -50	650	15	SOT 23	
BF 767 P	-30	-20	110	> 15	-3	-10	< -100	950	15	SOT 23	

Microwave transistors

Type PNP = P NPN = N	Maximum ratings				Characteristics ($T_{amb} = 25^\circ\text{C}$)								Package outlines	
	V_{CEO} V	I_C mA	P_{tot} mW	f_T MHz	NF (dB)	I_C mA	V_{CE} V	G_p dB	I_C mA	V_{CE} V	f MHz	R_g Ω	Pin configuration No.	Type
BFQ 17 N	25	150	1500	1200	< 6	30	15	16	70	18	200	60	16	SOT 89
BFQ 19 N	15	75	550	5000	4,5	60	8	9	60	8	800	60	16	SOT 89
BFQ 29 N	15	30	200	4000	2,1	4	6	-	-	-	800	60	14	SOT 23
BFQ 64 N	20	200	1500	3000	-	-	-	10	120	15	800	60	16	SOT 89
BFR 35 N	12	30	200	5000	2,0	2	6	14	15	6	800	60	14	SOT 23
BFR 92 N	15	30	200	5000	2,0	2	6	14	15	6	800	60	14	SOT 23
BFR 93 N	15	50	200	5000	2,8	10	8	13	25	8	800	60	14	SOT 23
BFS 17 N	15	25	200	1300	4,0	14	5	11	10	5	800	60	14	SOT 23
BFT 92 P	-15	-25	180	5000	2,7	2	10	18	14	10	500	R_{opt}	15	SOT 23
BFT 93 P	-12	-35	180	5000	2,4	2	5	16,5	30	5	500	R_{opt}	15	SOT 23

SIPMOS small-signal transistors

Type N channel	Maximum ratings			Characteristics ($T_{amb} = 25^\circ\text{C}$)				Package outlines	
	V_{DS} V	I_D mA	P_{tot} mW	I_{DSS} nA	V_{DS} V	$R_{DS(on)}$ Ω	$V_{GS(th)}$ V	Pin configuration No.	Type
BSS 87	200	500	4000	< 200	60	< 6	0,8...2,8	18	SOT 89